

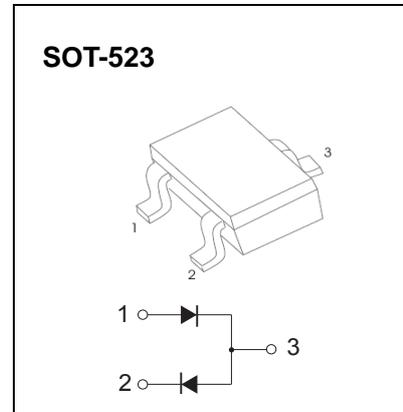
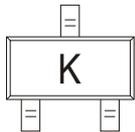
Plastic-Encapsulate Transistors

DA221T SWITCHING DIODE

FEATURES:

- Bias circuits
- Protection circuits

MARKING: K



Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	20	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	20	V
DC Blocking Voltage	V_R		V
Forward Continuous Current	I_{FM}	200	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Average Rectified Output Current	I_O	100	mA
Power Dissipation	P_D	150	mW
Thermal resistance From Junction to ambient	$R_{\theta JA}$	833	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	°C

Electrical Characteristics @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)}$	20			V	$I_R=100\mu A$
Forward voltage	V_F			1	V	$I_F=10mA$
Reverse current	I_R			0.1	μA	$V_R=15V$

Typical Characteristics

